

### DESCRIPTION

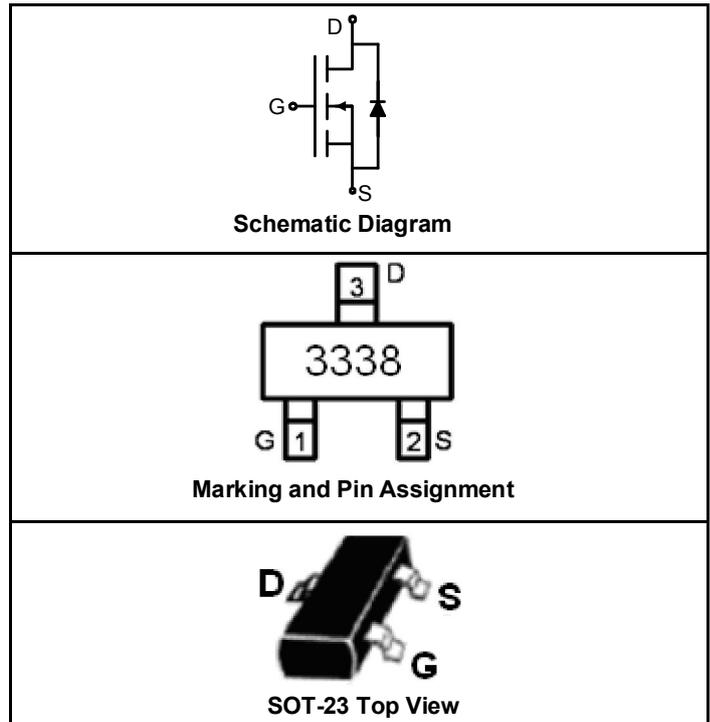
The SSF3338 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications.

### GENERAL FEATURES

- $V_{DS} = 30V, I_D = 4A$   
 $R_{DS(ON)} < 65m\Omega @ V_{GS}=4.5V$   
 $R_{DS(ON)} < 47m\Omega @ V_{GS}=10V$
- High Power and current handling capability
- Lead free product
- Surface Mount Package

### APPLICATIONS

- PWM applications
- Load switch
- Power management



### PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape Width	Quantity
3338	SSF3338	SOT-23	Ø330mm	12mm	3000 units

### ABSOLUTE MAXIMUM RATINGS ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D(25^\circ C)$	4	A
	$I_D(70^\circ C)$	3.5	A
	$I_{DM}$	20	A
Maximum Power Dissipation	$P_D$	1.25	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	130	$^\circ C/W$
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### ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V

Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$			0.5	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
<b>ON CHARACTERISTICS (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	3.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=2.8A$		41	65	m $\Omega$
		$V_{GS}=10V, I_D=3.5A$		30	47	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=2.5A$		7		S
<b>DYNAMIC CHARACTERISTICS (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$		310		PF
Output Capacitance	$C_{oss}$			60		PF
Reverse Transfer Capacitance	$C_{rss}$			30		PF
<b>SWITCHING CHARACTERISTICS (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=15V, V_{GS}=10V, R_{GEN}=6\Omega$ $I_D=1A$		7		nS
Turn-on Rise Time	$t_r$			12		nS
Turn-Off Delay Time	$t_{d(off)}$			15		nS
Turn-Off Fall Time	$t_f$			5		nS
Total Gate Charge	$Q_g$	$V_{DS}=15V, I_D=2.5A, V_{GS}=10V$		6		nC
Gate-Source Charge	$Q_{gs}$			2		nC
Gate-Drain Charge	$Q_{gd}$			1		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=1.25A$		0.8	1.2	V

### NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in<sup>2</sup> FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing.

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

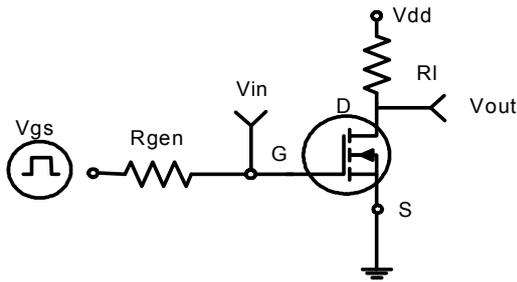


Figure 1: Switching Test Circuit

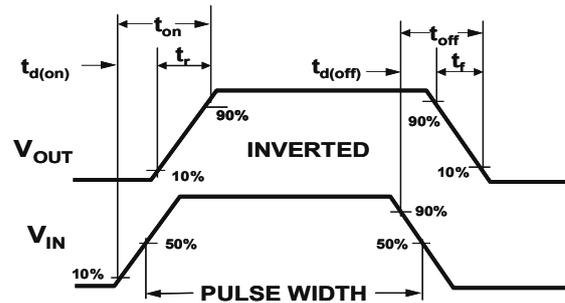


Figure 2: Switching Waveforms

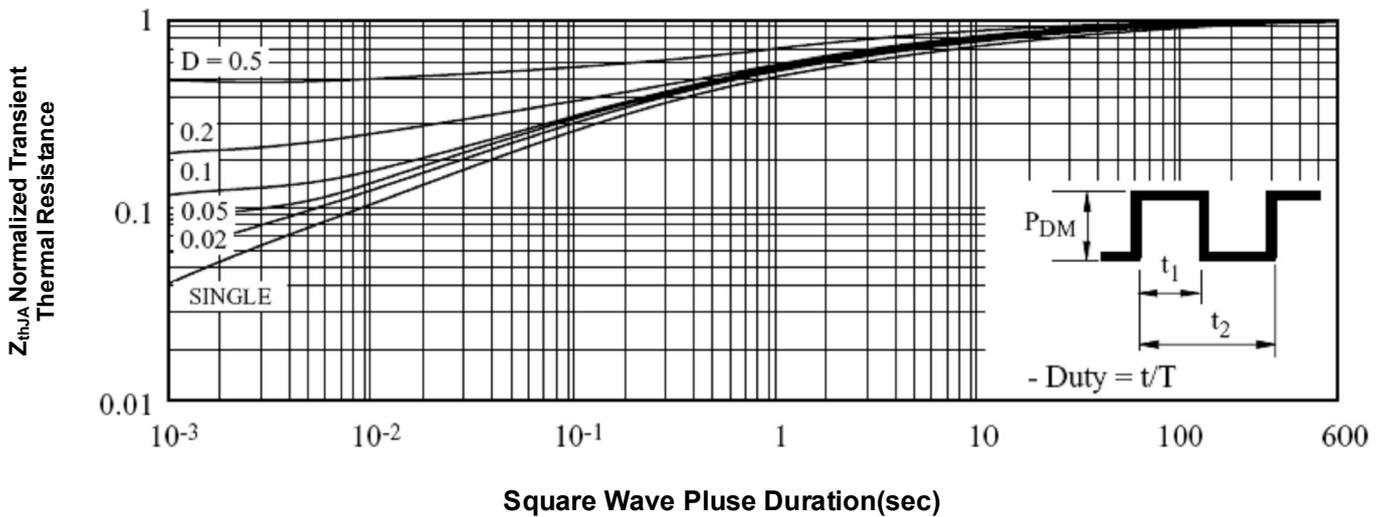
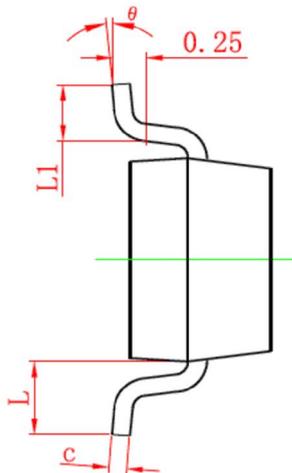
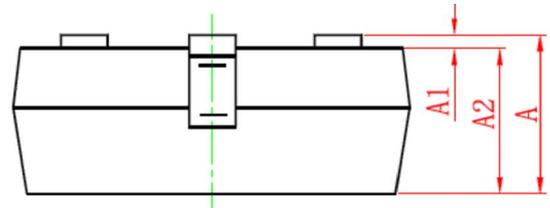
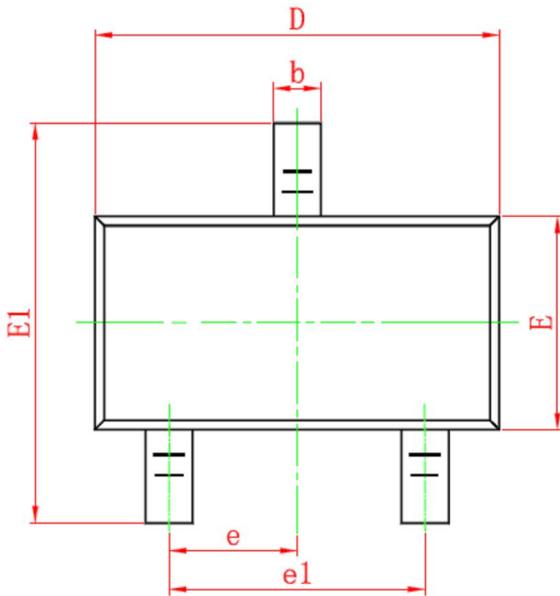


Figure 3: Normalized Maximum Transient Thermal Impedance

## SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT: mm)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
$\theta$	0°	8°

### NOTES:

- All dimensions are in millimeters.
- Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
- Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- Dimension L is measured in gauge plane.
- Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.